

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	7	contact same "trace stubs" and "I/O pad" and interconnection and circuit and (conduct\$4 or metal)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 11:22
L2	422	bump same "I/O pad"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 11:24
L3	3	bump same "I/O pad" and (p-well or n-well)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 11:24
L4	3	bump same "I/O pad" and ("p-well" or "n-well") and solder	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 11:24
L5	3	bump same "I/O pad" and ("p-well" or "n-well") and solder and bond\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 11:38
L6	5	"10237640"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 11:40
L7	2	"6927471"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 11:50
L8	7	"fluorinated silicone" and squeegee	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 11:51

L9	872	"fluorinated silicone"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 11:51
L10	7	"fluorinated silicone" and (substrate or semiconductor or wafer) and (dielectric or oxide) and "I/O pad"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 11:52
L11	237	"fluorinated silicone" and (substrate or semiconductor or wafer) and (dielectric or oxide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 11:52
L12	0	"fluorinated silicone" and (substrate or semiconductor or wafer) and (dielectric or oxide) and (p-well or n-well)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 11:52
L13	202	"fluorinated silicone" and (substrate or semiconductor or wafer) and (dielectric or oxide) and wells	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 11:52
L14	193	"fluorinated silicone" and (substrate or semiconductor or wafer) and (dielectric or oxide) and wells and (conduct\$4 or metal)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 11:53
L15	34	"fluorinated silicone" and (substrate or semiconductor or wafer) and (dielectric or oxide) and wells and (conduct\$4 or metal) and circuit	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 11:53
L16	13	"fluorinated silicone" and (substrate or semiconductor or wafer) and (dielectric or oxide) and wells and (conduct\$4 or metal) and circuit and interconnect	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 12:12

L17	301	(substrate or semiconductor or wafer) and (dielectric or oxide) and wells and (conduct\$4 or metal) and circuit and interconnect and squeegee	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 12:13
L18	117	(substrate or semiconductor or wafer) and (dielectric or oxide) and wells and (conduct\$4 or metal) and circuit and interconnect and squeegee and mask and bump	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 12:13
L19	1996711	(substrate or semiconductor or wafer) and (dielectric or oxide) and wells and (conduct\$4 or metal) and circuit and interconnect and squeegee and mask and bump polymer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 12:13
L20	84	(substrate or semiconductor or wafer) and (dielectric or oxide) and wells and (conduct\$4 or metal) and circuit and interconnect and squeegee and mask and bump and polymer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 12:14
L21	9	(substrate or semiconductor or wafer) and (dielectric or oxide) and wells and (conduct\$4 or metal) and circuit and interconnect and squeegee and mask and bump and polymer and "I/O pad"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 12:14
S1	0	"salmon.inv.."	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 15:30
S2	0	"salmon.inv."	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 15:30
S3	1971	salmon.inv.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 15:31

S4	11	(salmon.inv.) and carrier and dielectric and interconnect\$4 and pad\$4 and well\$4 and base and fill\$4 and conduct\$4 and bump and release and polymer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 15:45
S5	0	(salmon.inv.) and carrier and dielectric and interconnect\$4 and pad\$4 and well\$4 and base and fill\$4 and conduct\$4 and bump and release and polymer and mask and fluori\$8 and squeegee and solder and (clean or wash) and (heat or thermal) and bond	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 15:35
S6	0	(salmon.inv.) and carrier and dielectric and interconnect\$4 and pad\$4 and well\$4 and base and fill\$4 and conduct\$4 and bump and release and polymer and mask and fluori\$8 and squeegee and solder and (clean or wash) and (heat or thermal)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 15:35
S7	0	(salmon.inv.) and carrier and dielectric and interconnect\$4 and pad\$4 and well\$4 and base and fill\$4 and conduct\$4 and bump and release and polymer and mask and fluori\$8 and squeegee and solder	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 15:36
S8	0	(salmon.inv.) and carrier and dielectric and interconnect\$4 and pad\$4 and well\$4 and base and fill\$4 and conduct\$4 and bump and release and polymer and mask and fluori\$8 and squeegee	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 15:36
S9	396	carrier and dielectric and interconnect\$4 and pad\$4 and well\$4 and base and fill\$4 and conduct\$4 and bump and release and polymer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 15:46
S10	151	carrier and dielectric and interconnect\$4 and pad\$4 and well\$4 and base and fill\$4 and conduct\$4 and bump and release and polymer and (wash or clean) and (heat or thermal)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 15:50

S11	0	carrier and dielectric and interconnect\$4 and pad\$4 and well\$4 and base and fill\$4 and conduct\$4 and bump and release and polymer and (wash or clean) and (heat or thermal) and "fluorinated silicon"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 15:51
S12	0	carrier and dielectric and interconnect\$4 and pad\$4 and well\$4 and base and fill\$4 and conduct\$4 and bump and release and polymer and (wash or clean) and (heat or thermal) and fluorinate and silicone	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 15:52
S13	16	carrier and dielectric and interconnect\$4 and pad\$4 and well\$4 and base and fill\$4 and conduct\$4 and bump and release and polymer and (wash or clean) and (heat or thermal) and fluor\$6 and silicone	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 16:14
S14	5095	carrier and dielectric and interconnect\$4 and pad\$4 and well\$4 and fill\$4 and conduct\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 16:16
S15	10	carrier and dielectric and interconnect\$4 and pad\$4 and well\$4 and fill\$4 and conduct\$4 and bump and "fluorinated silicone"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 16:37
S16	4	"4862332"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 16:37
S17	53	"4862322"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 16:39
S18	159	(semiconductor or wafer or substrate) and dielectric and circuit and interconnect and "I/O pads" and well\$4 and fill and (conduct\$4 or metal)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 16:41

S19	114893	(semiconductor or wafer or substrate) and dielectric and circuit and interconnect and "I/O pads" and well\$4 and fill and (conduct\$4 or metal) and (open or via or hole) and bump ahd (heat\$4 or thermal\$4) and cool\$4 and solder and (clean or wash)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 16:43
S20	17	(semiconductor or wafer or substrate) and dielectric and circuit and interconnect and "I/O pads" and well\$4 and fill and (conduct\$4 or metal) and (open or via or hole) and bump and (heat\$4 or thermal\$4) and cool\$4 and solder and (clean or wash)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 16:59
S21	14	contact\$4 and "trace stub"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 16:59
S22	8	contact\$4 and "trace stub" and input and output and pad	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 17:00
S23	8	contact\$4 and "trace stub" and input and output and pad and (conduct\$4 or metal) and rout\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/28 17:00
S24	690	(dielectric or oxide) and interconnect and circuit and (open\$3 or via or hole or trench) and "I/O pads" and (conduct\$4 or metal) and wells	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 08:14
S25	0	(dielectric or oxide) and interconnect and circuit and (open\$3 or via or hole or trench) and "I/O pads" and (conduct\$4 or metal) and wells and squeegee	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 08:14
S26	11	(dielectric or oxide) and interconnect and circuit and (open\$3 or via or hole or trench) and "I/O pads" and (conduct\$4 or metal) and wells and squeegee	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 08:45

S27	136	(dielectric or oxide) and interconnect and circuit and (open\$3 or via or hole or trench) and "I/O pads" and (conduct\$4 or metal) and (p-well or n-well)	US;PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 08:45
S28	0	(dielectric or oxide) and interconnect and circuit and (open\$3 or via or hole or trench) and "I/O pads" and (conduct\$4 or metal) and (p-well or n-well) and squeegee	US;PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 08:46
S29	133	(dielectric or oxide) and interconnect and circuit and (open\$3 or via or hole or trench) and "I/O pads" and (conduct\$4 or metal) and (p-well or n-well) and (substrate or wafer or semiconductor)	US;PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 08:46
S30	30	(dielectric or oxide) and interconnect and circuit and (open\$3 or via or hole or trench) and "I/O pads" and (conduct\$4 or metal) and (p-well or n-well) and (substrate or wafer or semiconductor) and bump	US;PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 08:47
S31	27	(dielectric or oxide) and interconnect and circuit and (open\$3 or via or hole or trench) and "I/O pads" and (conduct\$4 or metal) and (p-well or n-well) and (substrate or wafer or semiconductor) and bump and mask and polymer	US;PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 08:47
S32	0	(dielectric or oxide) and interconnect and circuit and (open\$3 or via or hole or trench) and "I/O pads" and (conduct\$4 or metal) and (p-well or n-well) and (substrate or wafer or semiconductor) and bump and mask and polymer and "fluorinated silicone"	US;PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 08:47
S33	27	(dielectric or oxide) and interconnect and circuit and (open\$3 or via or hole or trench) and "I/O pads" and (conduct\$4 or metal) and (p-well or n-well) and (substrate or wafer or semiconductor) and bump and mask and polymer and rout\$4	US;PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 08:48

S34	0	(dielectric or oxide) and interconnect and circuit and (open\$3 or via or hole or trench) and "I/O pads" and (conduct\$4 or metal) and (p-well or n-well) and (substrate or wafer or semiconductor) and bump and mask and polymer and rout\$4 and bond and solder and (thermal or heat) and cool\$4 and (clean or wash)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 08:49
S35	0	(dielectric or oxide) and interconnect and circuit and (open\$3 or via or hole or trench) and "I/O pads" and (conduct\$4 or metal) and (p-well or n-well) and (substrate or wafer or semiconductor) and bump and mask and polymer and rout\$4 and bond and solder and (thermal or heat) and cool\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 08:49
S36	0	(dielectric or oxide) and interconnect and circuit and (open\$3 or via or hole or trench) and "I/O pads" and (conduct\$4 or metal) and (p-well or n-well) and (substrate or wafer or semiconductor) and bump and mask and polymer and rout\$4 and bond and solder and (thermal or heat)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 08:49
S37	0	(dielectric or oxide) and interconnect and circuit and (open\$3 or via or hole or trench) and "I/O pads" and (conduct\$4 or metal) and (p-well or n-well) and (substrate or wafer or semiconductor) and bump and mask and polymer and rout\$4 and bond and solder	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 08:50
S38	27	(dielectric or oxide) and interconnect and circuit and (open\$3 or via or hole or trench) and "I/O pads" and (conduct\$4 or metal) and (p-well or n-well) and (substrate or wafer or semiconductor) and bump and mask and polymer and rout\$4 and bond	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 08:52

S39	27	(dielectric or oxide) and interconnect and circuit and (open\$3 or via or hole or trench) and "I/O pads" and (conduct\$4 or metal) and (p-well or n-well) and (substrate or wafer or semiconductor) and bump and mask and polymer and rout\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 08:52
S40	27	(dielectric or oxide) and interconnect and circuit and (open\$3 or via or hole or trench) and "I/O pads" and (conduct\$4 or metal) and (p-well or n-well) and (substrate or wafer or semiconductor) and bump and mask and polymer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 08:52
S41	30	(dielectric or oxide) and interconnect and circuit and (open\$3 or via or hole or trench) and "I/O pads" and (conduct\$4 or metal) and (p-well or n-well) and (substrate or wafer or semiconductor) and bump and mask	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 11:19